

L Number	Hits	Search Text	DB	Time stamp
-	1366860	semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:51
-	3311	hydrogen near2 anneal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:07
-	2	(hydrogen near2 anneal\$4) with sublim\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:21
-	52	(hydrogen near2 anneal\$4) and sublim\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:22
-	2	(hydrogen near2 ((heat adj treatment) or anneal\$4)) with sublim\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 16:00
-	79	(hydrogen near2 ((heat adj treatment) or anneal\$4)) and sublim\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:26
-	4	(hydrogen near2 anneal\$4) same sublim\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:24
-	2580	(hydrogen near2 ((heat adj treatment) or anneal\$4)) and (insulat\$4 or (silicon adj dioxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:41
-	71	((hydrogen near2 ((heat adj treatment) or anneal\$4)) and (insulat\$4 or (silicon adj dioxide))) and (((first or upper) adj side) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:47
-	16	((hydrogen near2 ((heat adj treatment) or anneal\$4)) and (insulat\$4 or (silicon adj dioxide))) and (((first or upper) adj side) with substrate) and (((second or buttom) adj side) or underside) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:49
-	6168	semiconductor and sublim\$5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:51
-	12206	semiconductor and (insulat\$4 with (first or upper) with (second or buttom) with side)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:58

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-	7601	semiconductor and (substrate same (insulat\$4 with (first or upper) with (second or buttom) with side))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 15:59
-	91	(semiconductor and (substrate same (insulat\$4 with (first or upper) with (second or buttom) with side))) and (hydrogen near2 ((heat adj treatment) or anneal\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 16:01
-	14	((semiconductor and (substrate same (insulat\$4 with (first or upper) with (second or buttom) with side))) and (hydrogen near2 ((heat adj treatment) or anneal\$4))) and (etch\$4 with insulat\$5 with (first or upper) with substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/05/03 16:03